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(54) Title: PEROVSKITE SOLAR CELL

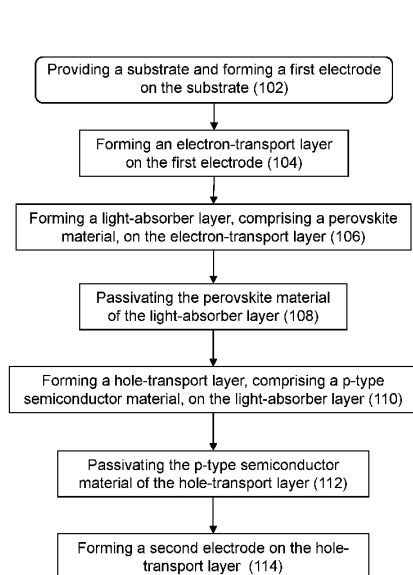


FIG. 3

(57) Abstract: The solar cell comprising a light-absorber layer comprising a perovskite material and a hole-transport layer comprising a p-type doped semiconductor material. The method comprises: forming the perovskite material on a substrate to define the light-absorber layer; forming the p-type doped semiconductor material on the substrate to define the hole-transport layer; and passivating one or more layers of the solar cell with a passivating medium comprising boron trifluoride, the one or more layers selected from the group consisting of: the light-absorber layer and the hole-transport layer. The step of passivating the one or more layers comprises directing a flow of gas comprising boron trifluoride towards said layers or the substrate said layers are to be formed on.

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